54-94-104MT..KPbF Series



Three Phase AC Switch (Power Modules), 50 A to 100 A



www.vishay.com

МТК

PRODUCT SUMMARY						
Ι _Ο	50 A to 100 A					
V _{RRM}	800 V to 1600 V					
Package	MT-K					
Circuit	Three phase AC switch					

FEATURES

• Package fully compatible with the industry standard INT-A-PAK power modules series



COMPLIANT

- High thermal conductivity package, electrically insulated case
- Outstanding number of power encapsulated components
- · Excellent power volume ratio
- 4000 V_{RMS} isolating voltage
- UL E78996 approved
- Designed and qualified for industrial level
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION

A range of extremely compact, encapsulated three phase AC switches offering efficient and reliable operation. They are intended for use in general purpose and heavy duty applications as control motor starter.

MAJOR RATINGS AND CHARACTERISTICS							
SYMBOL	CHARACTERISTICS	54MT.K	94MT.K	104MT.K	UNITS		
1		50	90	100	А		
I _O	T _C	80	80	80	°C		
1	50 Hz	390	950	1130	A		
I _{FSM}	60 Hz	410	1000	1180	A		
l ² t	50 Hz	770	4525	6380	A2a		
1-1	60 Hz	700	4130	5830	A ² s		
l²√t		7700	45250	63800	A²√s		
V _{RRM}	Range	800 to 1600 V					
T _{Stg}	Range	-40 to 125 °C					
TJ	Range		-40 to 125		°C		



ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS									
TYPE NUMBER	VOLTAGE CODE	V _{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM REPETITIVE PEAK OFF-STATE VOLTAGE, GATE OPEN CIRCUIT V	I _{RRM} /I _{DRM} , MAXIMUM AT T _J = 125 °C mA				
	80	800	900	800					
	100	1000	1100	1000					
54MTK	120	1200	1300	1200	20 (1)				
	140	1400	1500	1400					
	160	1600	1700	1600					
	80	800	900	800					
	100	1000	1100	1000					
94/104MTK	120	1200	1300	1200	40 (1)				
	140	1400	1500	1400					
	160	1600	1700	1600					

Note

⁽¹⁾ For single AC switch

FORWARD CONDUCT	ION							
PARAMETER	SYMBOL		TEST CONDITION	ONS	54MT.K	94MT.K	104MT.K	UNITS
Maximum I _{RMS} output current		For all condu	For all conduction angle		50	90	100	Α
at case temperature	Ι _Ο	For all condu	iction angle		80	80	80	°C
		t = 10 ms	No voltage		390	950	1130	
Maximum peak, one-cycle forward, non-repetitive		t = 8.3 ms	reapplied		410	1000	1180	A
on state surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		330	800	950	A
		t = 8.3 ms	reapplied	Initial T _J = T _J	345	840	1000	
		t = 10 ms	No voltage	maximum	770	4525	6380	
Moving up 12t for fusing	l ² t	t = 8.3 ms	reapplied		700	4130	5830	A ² s
Maximum I ² t for fusing	1-1	t = 10 ms	100 % V _{BBM}		540	3200	4510	A²s
		t = 8.3 ms rea	reapplied		500	2920	4120	
Maximum I ² \sqrt{t} for fusing	l²√t	t = 0.1 to 10	ms, no voltage r	eapplied	7700	45 250	63 800	A²√s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π >	$I_{T(AV)} < I < \pi \times I_{T}$	1.16	0.99	0.99	v	
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$, T _J maximum	1.44	1.19	1.15	v	
Low level value on-state slope resistance	r _{t1}	16.7 % x π x	$I_{T(AV)} < I < \pi \times I_{T}$	12.54	4.16	3.90		
High level value on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)})$, T _J maximum	11.00	3.56	3.48	mΩ	
Maximum on-state voltage drop	V _{TM}	l _{pk} = 150 A, 1 t _p = 400 μs s	Γ _J = 25 °C ingle junction	2.68	1.55	1.53	V	
Maximum non-repetitve rate of rise of turned on current	dl/dt	$ \begin{array}{l} T_{J} = 25 \ ^{\circ}\text{C}, \ \text{from } 0.67 \ \text{V}_{\text{DRM}}, \ \text{I}_{\text{TM}} = \pi \ \text{x} \ \text{I}_{\text{T(AV)}}, \\ I_{g} = 500 \ \text{mA}, \ t_{r} < 0.5 \ \mu\text{s}, \ t_{p} > 6 \ \mu\text{s} \end{array} $				150		A/µs
Maximum holding current	Ι _Η	T _J = 25 °C, a	$T_J = 25 ^{\circ}$ C, anode supply = 6 V, resistive load, grate open circuit			200		mA
Maximum latching current	١L	T _J = 25 °C, a	node supply = 6	V, resistive load		400		1

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BLOCKING

BEOCKING						
PARAMETER	SYMBOL	TEST CONDITIONS	54MT.K	94MT.K	104MT.K	UNITS
RMS isolation voltage	V _{INS}	$T_J = 25 \text{ °C}$ all terminal shorted f = 50 Hz, t = 1 s	4000		V	
Maximum critical rate of rise of off-state voltage	dV/dt ⁽¹⁾	$T_{\rm J} = T_{\rm J}$ maximum, linear to 0.67 V _{DRM} , 500 gate open circuit			V/µs	

Note

⁽¹⁾ Available with dV/dt = 1000 V/ μ s, to complete code add S90 i. e. 104MT160KBS90

TRIGGERING							
PARAMETER	SYMBOL		TEST CONDITIONS 54MT.K 94MT.K 104MT.K				
Maximum peak gate power	P _{GM}				10		w
Maximum average gate power	P _{G(AV)}				2.5		vv
Maximum peak gate current	I _{GM}	T _J = T _J maxir	num		2.5		А
Maximum peak negative gate voltage	- V _{GT}				10		
		$T_J = 40 \ ^{\circ}C$	$T_J = 40 \ ^{\circ}C$		4.0		V
Maximum required DC gate voltage to trigger	V _{GT}	T _J = 25 °C]	2.5			
		$T_J = 125 \text{ °C}$ Anode supply = 6 V, resistive 1.7					
		T _J = -40 °C	T _J = -40 °C load		270		
Maximum required DC gate current to trigger	I _{GT}	T _J = 25 °C			150		mA
		T _J = 125 °C			80		
Maximum gate voltage that will not trigger	V_{GD}	T T movimum rated // applied			0.25		V
Maximum gate current that will not trigger	I _{GD}	ij= ij maxir	$T_J = T_J$ maximum, rated V_{DRM} applied		6		mA

THERMAL AND MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	54MT.K	94MT.K	104MT.K	UNITS			
Maximum junction operating and storage temperature range	T _J , T _{Stg}			-40 to 125					
		DC operation per single AC switch	0.52	0.39	0.34				
Maximum thermal resistance,	Р	DC operation per junction	1.05	0.77	0.69				
junction to case R _{thJC}		180 °C sine cond. angle per single AC switch	0.56	0.40	0.36	36 K/W			
		180 °C sine cond. angle per junction	1.12	0.80	0.72				
Maximum thermal resistance, case to heatsink	R _{thCS}	Per module Mounting surface smooth, flat and grased	0.03						
Mounting to heatsink		A mounting compound is recommended and		4 to 6		Nm			
to terminal		the torque should be rechecked after a period of 3 hours to allow for the spread of		3 to 4					
Approximate weight		 period of 3 hours to allow for the spread of the compound. Lubricated threads. 			g				

DEVICES		SINUSOIDAL CONDUCTION AT T _J MAXIMUM					RECTANGULAR CONDUCTION AT T _J MAXIMUM				
	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	
54MT.K	0.072	0.085	0.108	0.152	0.233	0.055	0.091	0.117	0.157	0.236	
94MT.K	0.033	0.039	0.051	0.069	0.099	0.027	0.044	0.055	0.071	0.100	K/W
104MT.K	0.027	0.033	0.042	0.057	0.081	0.023	0.037	0.046	0.059	0.082	

Note

Table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

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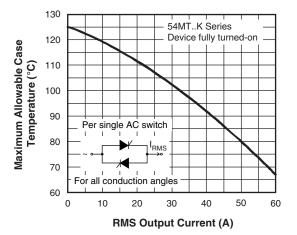


Fig. 1 - Current Ratings Characteristic

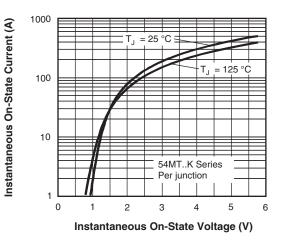
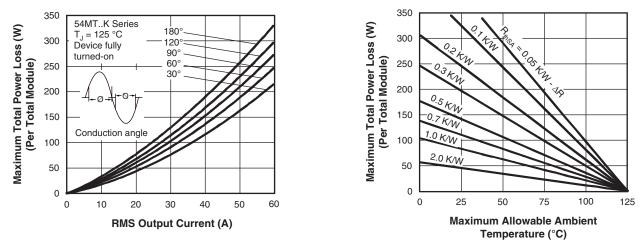
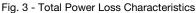
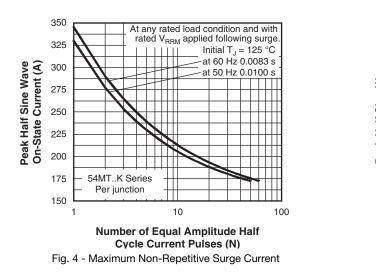
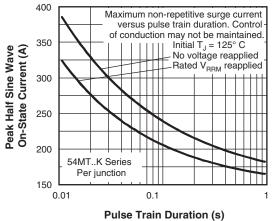


Fig. 2 - Forward Voltage Drop Characteristics











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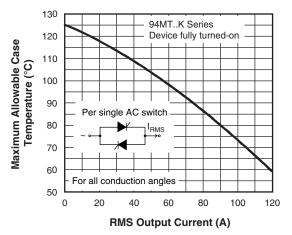


Fig. 6 - Current Ratings Characteristic

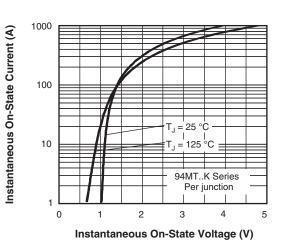


Fig. 7 - Forward Voltage Drop Characteristics

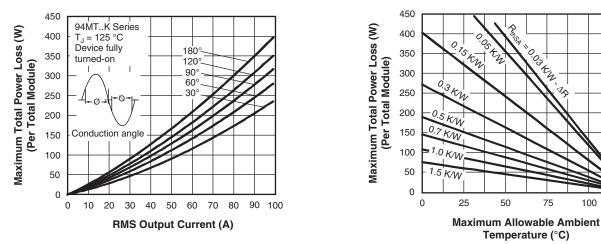
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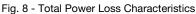
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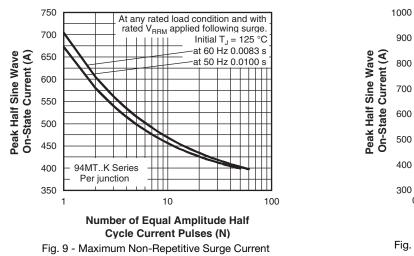
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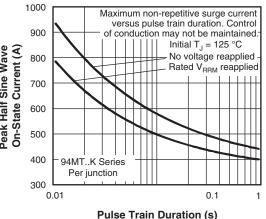
100

125









50

Temperature (°C)

Fig. 10 - Maximum Non-Repetitive Surge Current

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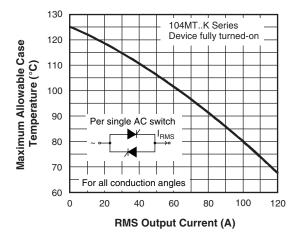
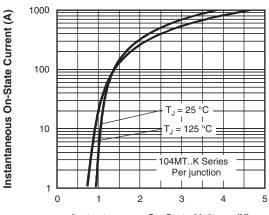


Fig. 11 - Current Ratings Characteristic



Instantaneous On-State Voltage (V)

Fig. 12 - Forward Voltage Drop Characteristics

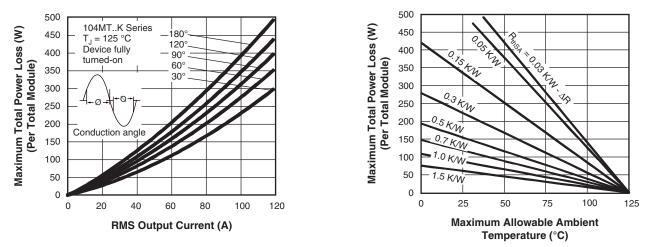


Fig. 13 - Total Power Loss Characteristics

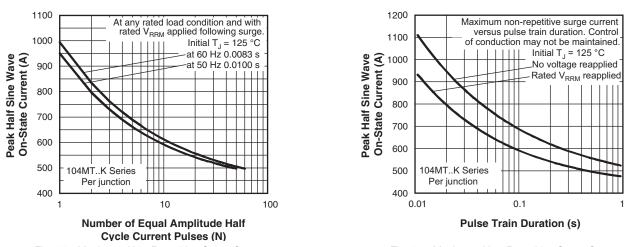
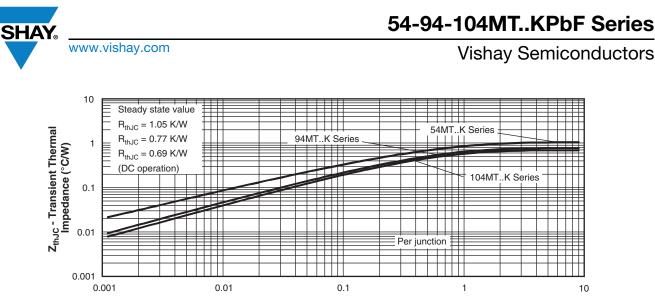


Fig. 14 - Maximum Non-Repetitive Surge Current

Fig. 15 - Maximum Non-Repetitive Surge Current

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Square Wave Pulse Duration (s)

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Fig. 16 - Thermal Impedance ZthJC Characteristics

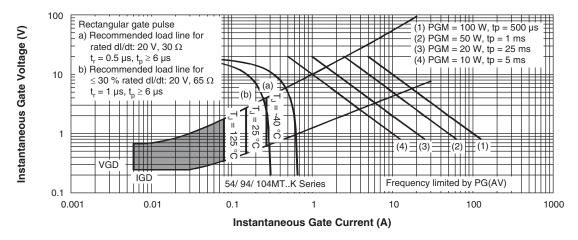
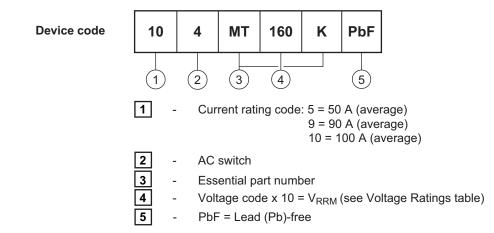


Fig. 17 - Gate Characteristics

ORDERING INFORMATION TABLE



Note

• To order the optional hardware go to www.vishay.com/doc?95172

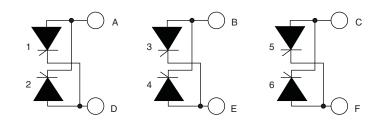
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CIRCUIT CONFIGURATION



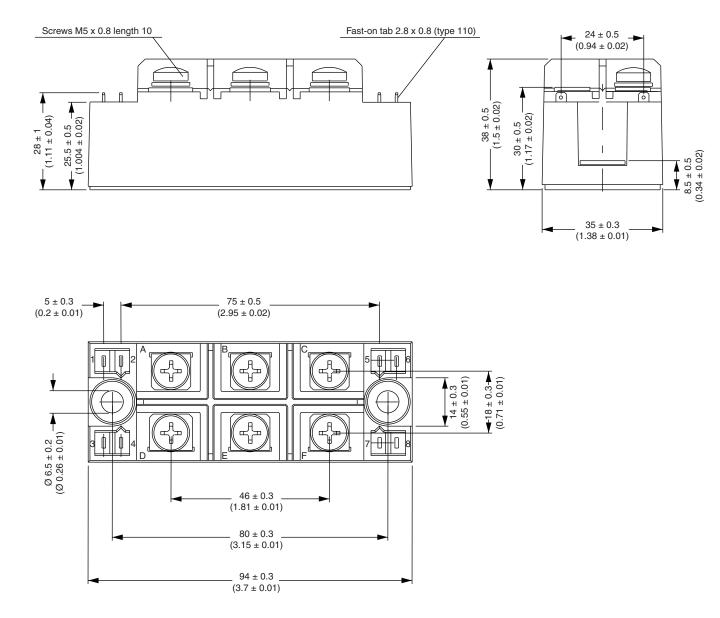
LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95004				



MTK (with and without optional barrier)

DIMENSIONS WITH OPTIONAL BARRIERS in millimeters (inches)

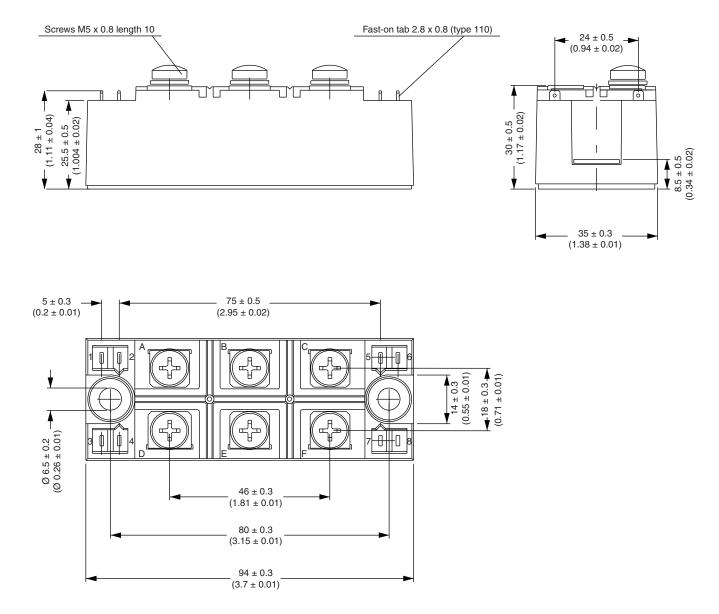
SHAY



Vishay Semiconductors MTK (with and without optional barrier)



DIMENSIONS WITHOUT OPTIONAL BARRIERS in millimeters (inches)





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